

### FDFS2P102

### **Integrated P-Channel MOSFET and Schottky Diode**

### **General Description**

The FDFS2P102 combines the exceptional performance of Fairchild's high cell density MOSFET with a very low forward voltage drop Schottky barrier rectifier in an SO-8 package.

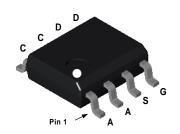
This device is designed specifically as a single package solution for DC to DC converters. It features a fast switching, low gate charge MOSFET with very low on-state resistance. The independently connected Schottky diode allows its use in a variety of DC/DC converter topologies.

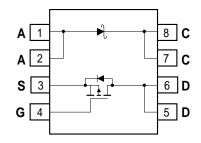
### **Applications**

- DC/DC converters
- Load Switch
- Motor Drives

### **Features**

- -3.3 A, -20 V.  $R_{DS(ON)} = 0.125 \ \Omega \ @V_{GS} = -10 \ V$   $R_{DS(ON)} = 0.200 \ \Omega \ @V_{GS} = -4.5 \ V.$
- $V_F < 0.39 V @ 1 A (T_J = 125 {}^{o}C)$ .  $V_F < 0.47 V @ 1 A$ .  $V_F < 0.58 V @ 2 A$ .
- Schottky and MOSFET incorporated into single power surface mount SO-8 package.
- Electrically independent Schottky and MOSFET pinout for design flexibility.





MOSFET Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-20	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-3.3	А
	- Pulsed		-20	
P <sub>D</sub>	Power Dissipation for Dual Operation		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Rang	е	-55 to +150	°C

Schottky Diode Maximum Ratings TA=25°C unless otherwise noted

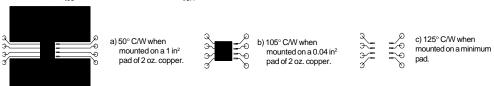
$V_{RRM}$	Repetitive Peak Reverse Voltage		20	V
Io	Average Forward Current	(Note 1a)	1	Α

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDFS2P102	FDFS2P102	13	12mm	2500 units

Symbol	Parameter	Test C	onditions	Min	Тур	Max	Units
Off Char	acteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D$	= -250 µA	-20			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V},$	*			-1	μΑ
	-	$V_{GS} = 0 V$	$T_J = 55^{\circ}C$			-10	
I <sub>GSSF</sub>	Gate-Body Forward Leakage	$V_{GS} = 20 \text{ V}, \text{ V}$	<sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Reverse Leakage	$V_{GS} = -20 \text{ V},$	$V_{DS} = 0 V$			-100	nA
On Char	acteristics (Note 2)	•		•			
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D}$	= -250 µA	-1	-1.4	-2	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, \text{ I}$			0.100	0.125	Ω
**DS(0II)	Statio Brain Source on Resistance	$V_{GS} = -4.5 \text{ V},$			0.167	0.2	
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = -10 V, V		-10			Α
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -10 V, I			5		S
	Characteristics				!	!	
Dynamic C <sub>iss</sub>	Characteristics Input Capacitance	V <sub>DS</sub> = -10 V, V	$V_{GS} = 0 \text{ V}.$		270		pF
Coss	Output Capacitance	f = 1.0 MHz		150		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	1			45		pF
Switchin t <sub>d(on)</sub>	<b>G Characteristics</b> (Note 2)  Turn-On Delay Time	V <sub>DD</sub> = -15 V,	I <sub>D</sub> = -1 A,		8	16	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -10 \text{ V}, \text{ I}$	$R_{GEN} = 6 \Omega$		7	14	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	1			17	27	ns
t <sub>f</sub>	Turn-Off Fall Time				10	1.8	ns
Qg	Total Gate Charge	$V_{DS} = -5 \text{ V}, I_{D}$ $V_{GS} = -10 \text{ V},$	= -3.3 A,		7	10	nC
Drain-Sc	ource Diode Characteristics ar	nd Maximur	n Ratings				
ls	Maximum Continuous Drain-Source D	iode Forward C	Current			-1.3	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S}$	= -1.3 A (Note 2)		-0.8	-1.2	V
Schottky	/ Diode Characteristics						
I <sub>R</sub>	Reverse Leakage	V <sub>R</sub> = 20 V	$T_J = 25^{\circ}C$			250	uA
	J		$T_J = 125^{\circ}C$			18	mA
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 1 A	$T_J = 25^{\circ}C$			0.47	V
			$T_{J} = 125^{\circ}C$			0.39	
		$I_F = 2 A$	$T_{J} = 25^{\circ}C$			0.58	
	<u> </u>		$T_{\rm J} = 125^{\circ}{\rm C}$			0.53	
	Characteristics						ï
R JA	Thermal Resistance, Junction-to-Ambi	ent	(Note 1a)		78		
R <sub>JC</sub>	Thermal Resistance, Junction-to-Case		40				

<sup>1:</sup> R<sub>BUA</sub> is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



Scale 1: 1 on letter size paper

<sup>2:</sup> Pulse Test: Pulse Width  $\leq\!300\,\mu\text{s},$  Duty Cycle  $\leq\!2.0\%$ 

### **Typical Characteristics**

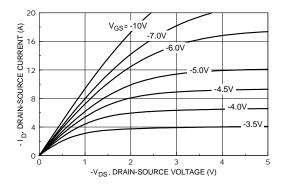


Figure 1. On-Region Characteristics.

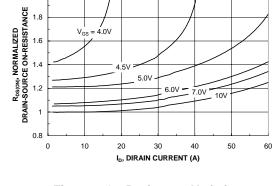


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

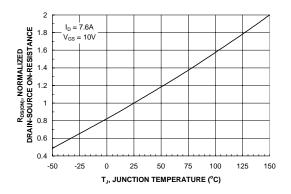


Figure 3. On-Resistance Variation with Temperature.

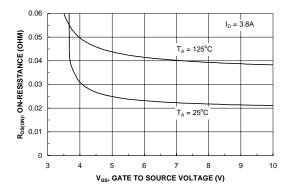


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

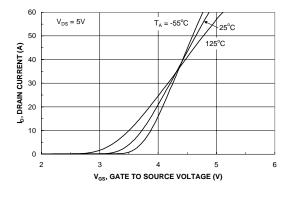


Figure 5. Transfer Characteristics.

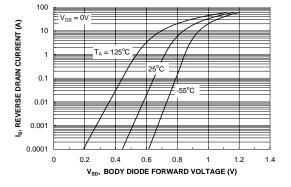
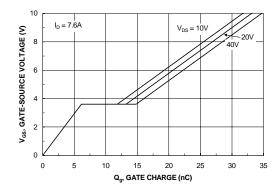


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics (continued)



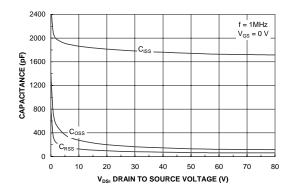
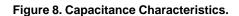
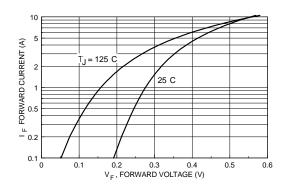


Figure 7. Gate-Charge Characteristics.





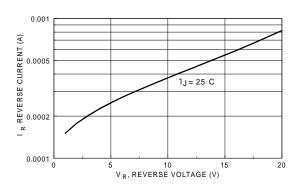


Figure 9. Schottky Diode Forward Voltage.

Figure 10. Schottky Diode Reverse Current.

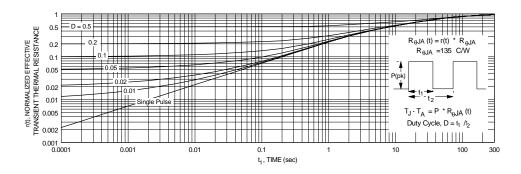


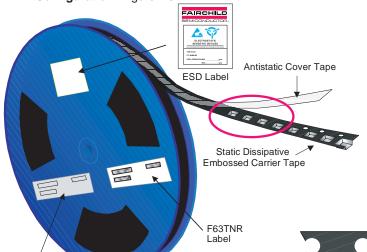
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.

### **SOIC-8 Tape and Reel Data**



### SOIC(8lds) Packaging Configuration: Figure 1.0



Packaging	Description

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 330cm diameter reel. The relea are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.

**ESD Label** 

F63TN Label





SOIC (8lds) Packaging Information Standard no flow code) **Packaging Option** L86Z F011 D84Z Rail/Tube TNR TNR Packaging type TNR Qty per Reel/Tube/Bag 2.500 4.000 500 Reel Size 13" Dia 13" Dia 7" Dia Box Dimension (mm) 343x64x343 530x130x83 343x64x343 184x187x47 Max qty per Box 5,000 30,000 8,000 1,000 Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 0.1182 Weight per Reel (kg) 0.6060 0.9696

**SOIC-8 Unit Orientation** 

343mm x 342mm x 64mm Standard Intermediate box

### F63TNR Label sample

Customized Label

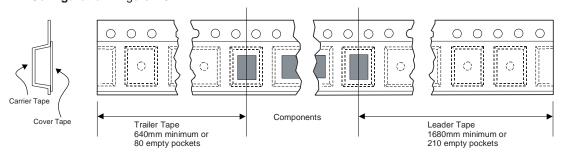
Note/Comments



# SPEC: SPEC REV: CPN: N/F: F (F63TNR)3

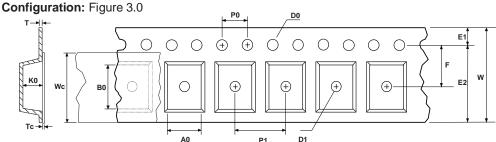
F63TNI

## **SOIC(8lds) Tape Leader and Trailer Configuration:** Figure 2.0





### SOIC(8lds) Embossed Carrier Tape



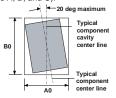


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

Component Rotation

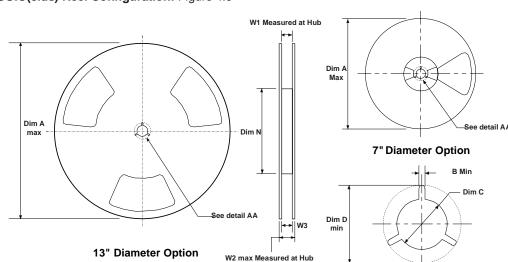


Sketch C (Top View)

Component lateral movement

DETAIL AA

### SOIC(8lds) Reel Configuration: Figure 4.0

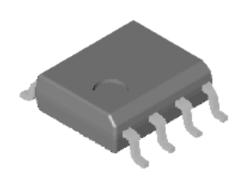


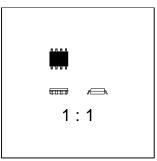
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

### **SOIC-8 Package Dimensions**



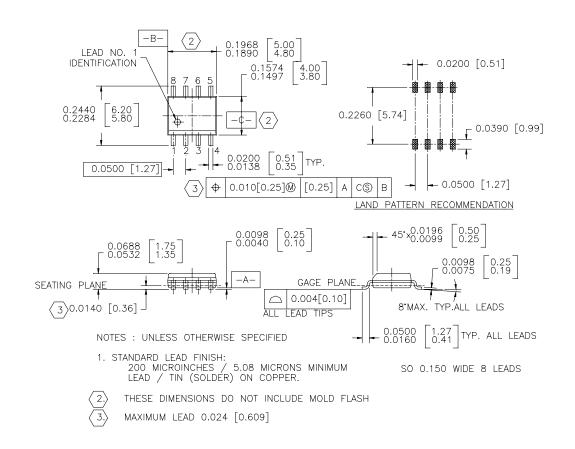
### SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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CROSSVOLT™ HiSeC™ Quiet Series™ DOME™ ISOPLANAR™ SuperSOT™-3 E<sup>2</sup>CMOS<sup>TM</sup> MICROWIRE™ SuperSOT™-6 OPTOLOGIC™ EnSigna™ SuperSOT™-8 FACT™ OPTOPLANAR™ SyncFET™ POP™ FACT Quiet Series™ TinyLogic™

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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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